

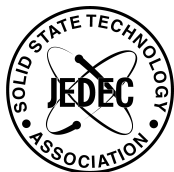
JEDEC STANDARD

Double Data Rate (DDR) SDRAM Specification

JESD79

JUNE 2000

JEDEC SOLID STATE TECHNOLOGY ASSOCIATION



Samsung Electronics Co., Ltd.

NOTICE

JEDEC standards and publications contain material that has been prepared, reviewed, and approved through the JEDEC Board of Directors level and subsequently reviewed and approved by the EIA General Counsel.

JEDEC standards and publications are designed to serve the public interest through eliminating misunderstandings between manufacturers and purchasers, facilitating interchangeability and improvement of products, and assisting the purchaser in selecting and obtaining with minimum delay the proper product for use by those other than JEDEC members, whether the standard is to be used either domestically or internationally.

JEDEC standards and publications are adopted without regard to whether or not their adoption may involve patents or articles, materials, or processes. By such action JEDEC does not assume any liability to any patent owner, nor does it assume any obligation whatever to parties adopting the JEDEC standards or publications.

The information included in JEDEC standards and publications represents a sound approach to product specification and application, principally from the solid state device manufacturer viewpoint. Within the JEDEC organization there are procedures whereby a JEDEC standard or publication may be further processed and ultimately become an ANSI/EIA standard.

No claims to be in conformance with this standard may be made unless all requirements stated in the standard are met.

Inquiries, comments, and suggestions relative to the content of this JEDEC standard or publication should be addressed to JEDEC Solid State Technology Association, 2500 Wilson Boulevard, Arlington, VA 22201-3834, (703)907-7560/7559 or www.jedec.org

Published by
JEDEC Solid State Technology Association 2000
2500 Wilson Boulevard
Arlington, VA 22201-3834

This document may be downloaded free of charge, however EIA retains the copyright on this material. By downloading this file the individual agrees not to charge for or resell the resulting material.

**PRICE: Please refer to the current
Catalog of JEDEC Engineering Standards and Publications or call Global Engineering
Documents, USA and Canada (1-800-854-7179), International (303-397-7956)**

Printed in the U.S.A.
All rights reserved

Samsung Electronics Co., Ltd

PLEASE!

DON'T VIOLATE
THE
LAW!

This document is copyrighted by the Electronic Industries Alliance and may not be reproduced without permission.

Organizations may obtain permission to reproduce a limited number of copies through entering into a license agreement. For information, contact:

JEDEC Solid State Technology Association
2500 Wilson Boulevard
Arlington, Virginia 22201-3834
or call (703) 907-7559

Samsung Electronics Co., Ltd.

Double Data Rate (DDR) SDRAM Specification

(The material contained in this standard was formulated under the cognizance of the JC-42.3 Subcommittee on RAM Memories and approved by the JEDEC Board of Directors. The text in this standard is from the following BoD Ballots: JCB-99-70, JCB-99-84, JCB-00-08, JCB-00-10, JCB-00-11, JCB-00-12, JCB-00-13, and JCB-00-23.)

1 Purpose

To define the minimum set of requirements for JEDEC-compliant 64M x4/x8/x16 DDR SDRAMs. System designs based on the required aspects of this specification will be supported by all DDR SDRAM vendors providing JEDEC compliant devices.

2 Scope

This comprehensive standard defines all required aspects of 64M x4/x8/x16 DDR SDRAMs, including features, functionality, AC and DC parametrics, packages and pin assignments. This scope will subsequently be expanded to formally apply to x32 devices, and higher density devices as well.

DOUBLE DATA RATE (DDR) SDRAM SPECIFICATION

16 M x4 (4 M x4 x4 banks), 8 M x8 (2 M x8 x4 banks), 4 M x16 (1 M x16 x4 banks)

FEATURES

- Double-data-rate architecture; two data transfers per clock cycle
- Bidirectional, data strobe (DQS) is transmitted/received with data, to be used in capturing data at the receiver
- DQS is edge-aligned with data for READs; center-aligned with data for WRITEs
- Differential clock inputs (CK and $\overline{\text{CK}}$)
- DLL aligns DQ and DQS transitions with CK transitions
- Commands entered on each positive CK edge; data and data mask referenced to both edges of DQS
- Four internal banks for concurrent operation
- Data mask (DM) for write data
- Burst lengths: 2, 4, or 8
- CAS Latency: 2 or 2.5
- AUTO PRECHARGE option for each burst access
- Auto Refresh and Self Refresh Modes
- 15.6 μs Maximum Average Periodic Refresh Interval
- 2.5 V (SSTL_2 compatible) I/O
- VDDQ = +2.5 V \pm 0.2 V
- VDD = +3.3 V \pm 0.3 V or +2.5 V \pm 0.2 V

GENERAL DESCRIPTION

The 64 Mb DDR SDRAM is a high-speed CMOS, dynamic random-access memory containing 67,108,864 bits. It is internally configured as a quad-bank DRAM.

The 64 Mb DDR SDRAM uses a double-data-rate architecture to achieve high-speed operation. The double data rate architecture is essentially a 2n pre-fetch architecture with an interface designed to transfer two data words per clock cycle at the I/O pins. A single read or write access for the 64 Mb DDR SDRAM effectively consists of a single 2n-bit wide, one clock cycle data transfer at the internal DRAM core and two corresponding n-bit wide, one-half-clock-cycle data transfers at the I/O pins.

A bidirectional data strobe (DQS) is transmitted externally, along with data, for use in data capture at the receiver. DQS is a strobe transmitted by the DDR SDRAM during READs and by the memory controller during WRITEs. DQS is edge-aligned with data for READs and center-aligned with data for WRITEs.

The 64 Mb DDR SDRAM operates from a differential clock (CK and $\overline{\text{CK}}$; the crossing of CK going HIGH and

$\overline{\text{CK}}$ going LOW will be referred to as the positive edge of CK). Commands (address and control signals) are registered at every positive edge of CK. Input data is registered on both edges of DQS, and output data is referenced to both edges of DQS, as well as to both edges of CK.

Read and write accesses to the DDR SDRAM are burst oriented; accesses start at a selected location and continue for a programmed number of locations in a programmed sequence. Accesses begin with the registration of an ACTIVE command, which is then followed by a READ or WRITE command. The address bits registered coincident with the ACTIVE command are used to select the bank and row to be accessed. The address bits registered coincident with the READ or WRITE command are used to select the bank and the starting column location for the burst access.

The DDR SDRAM provides for programmable read or write burst lengths of 2, 4 or 8 locations. An AUTO PRECHARGE function may be enabled to provide a self-timed row precharge that is initiated at the end of the burst access.

As with standard SDRAMs, the pipelined, multibank architecture of DDR SDRAMs allows for concurrent operation, thereby providing high effective bandwidth by hiding row precharge and activation time.

An auto refresh mode is provided, along with a power-saving, power-down mode. All inputs are compatible with the JEDEC Standard for SSTL_2. All outputs are SSTL_2, Class II compatible.

Initial devices will have a VDD supply of 3.3 V (nominal). Eventually, all devices will migrate to a VDD supply of 2.5 V (nominal). During this initial period of product availability, this split will be vendor and device specific.

This data sheet includes all features and functionality required for JEDEC DDR devices; options not required, but listed, are noted as such. Certain vendors may elect to offer a superset of this specification by offering improved timing and/or including optional features. Users benefit from knowing that any system design based on the required aspects of this specification are supported by all DDR SDRAM vendors; conversely, users seeking to use any superset specifications bear the responsibility to verify support with individual vendors.

Note: The functionality described in, and the timing specifications included in this data sheet are for the DLL Enabled mode of operation.

Note: This specification defines the minimum set of requirements for JEDEC 64 M x4/x8/x16 DDR SDRAMs. Vendors will provide individual data sheets in their specific format. Vendor data sheets should be consulted for optional features or superset specifications.

Release 1

Explore Litigation Insights

Docket Alarm provides insights to develop a more informed litigation strategy and the peace of mind of knowing you're on top of things.

Real-Time Litigation Alerts



Keep your litigation team up-to-date with **real-time alerts** and advanced team management tools built for the enterprise, all while greatly reducing PACER spend.

Our comprehensive service means we can handle Federal, State, and Administrative courts across the country.

Advanced Docket Research



With over 230 million records, Docket Alarm's cloud-native docket research platform finds what other services can't. Coverage includes Federal, State, plus PTAB, TTAB, ITC and NLRB decisions, all in one place.

Identify arguments that have been successful in the past with full text, pinpoint searching. Link to case law cited within any court document via Fastcase.

Analytics At Your Fingertips



Learn what happened the last time a particular judge, opposing counsel or company faced cases similar to yours.

Advanced out-of-the-box PTAB and TTAB analytics are always at your fingertips.

API

Docket Alarm offers a powerful API (application programming interface) to developers that want to integrate case filings into their apps.

LAW FIRMS

Build custom dashboards for your attorneys and clients with live data direct from the court.

Automate many repetitive legal tasks like conflict checks, document management, and marketing.

FINANCIAL INSTITUTIONS

Litigation and bankruptcy checks for companies and debtors.

E-DISCOVERY AND LEGAL VENDORS

Sync your system to PACER to automate legal marketing.